



DPLS350Y

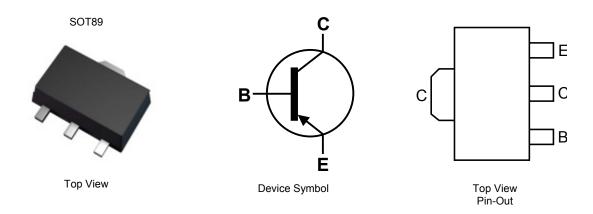
50V PNP LOW SATURATION POWER TRANSISTOR IN SOT89

Features

- BV_{CEO} > -50V
- I_C = -3A High Continuous Collector Current
- I_{CM} up to -5A Peak Pulse Current
- 2W Power Dissipation
- Low Saturation Voltage V_{CE(sat)} < -180mV @ 1A
- R_{CE(sat)} = 67mΩ @ 2A for a Low Equivalent On-Resistance
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (@3)
- Weight: 0.052 grams (Approximate)



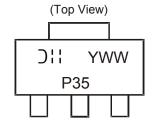
Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DPLS350Y-13	P35	13	12	2,500
DPLS350Y-13R	P35	13	12	4,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information



P35 = Product Type Marking Code: YWW = Date Code Marking Y = Last digit of year ex: 1 = 2011 WW = Week code 01 - 52



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-6	V
Continuous Collector Current	Ic	-3	Α
Peak Pulse Current	I _{CM}	-5	Α
Base Current	I _B	-500	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		1		
Power Dissipation	(Note 6)	P_{D}	1.6	W	
	(Note 7)		2.0	1	
	(Note 5)		125		
Thermal Resistance, Junction to Ambient Air	(Note 6)	$R_{ heta JA}$	78	°C/W	
	(Note 7)		62.5		
Thermal Resistance, Junction to Lead	(Note 8)	$R_{ heta JL}$	5.7	°C/W	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 9)

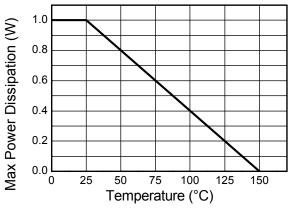
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

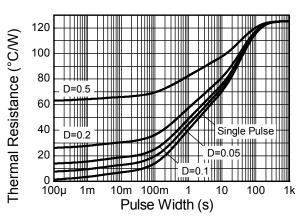
Notes:

- 5. For a device mounted with the exposed collector pad on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as note (5), except the device is mounted on 25mm x 25mm 1oz copper.
- 7. Same as note (5), except the device is mounted on 50mm x 50mm 1oz copper.
- 8. Thermal resistance from junction to solder-point (on the exposed collector pad).
 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



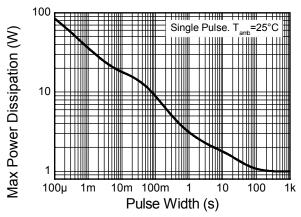
Thermal Characteristics and Derating Information



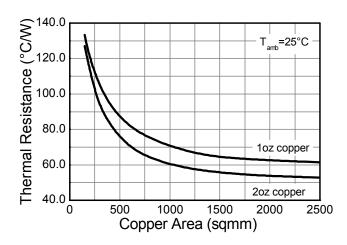


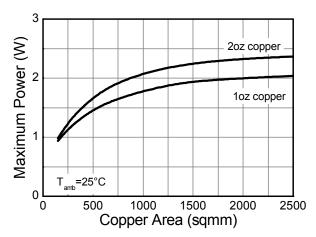
Derating Curve

Transient Thermal Impedance



Pulse Power Dissipation







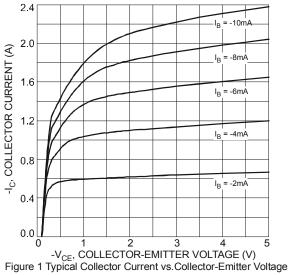
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
Collector-Base Breakdown Voltage	BV _{CBO}	-50	_	_	V	I _C = -100μA	
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	-50	_	_	V	I _C = -10mA	
Emitter-Base Breakdown Voltage	BV _{EBO}	-6	_	_	V	I _E = -100μA	
Collector-Emitter Cut-off Current	I _{CES}	_	_	-100	nA	V _{CE} = -50V	
Collector Cut-off Current		_	_	-100	nA	V _{CB} = -50V	
Collector Cut-on Current	I _{CBO}			-50	μA	V _{CB} = -50V, T _A = +150°C	
Emitter Cut-off Current	I _{EBO}	_	_	-100	nA	V _{EB} = -5V	
		200		_		I _C = -100mA, V _{CE} = -2V	
		200		_		I _C = -500mA, V _{CE} = -2V	
Static Forward Current Transfer Ratio (Note 10)	h _{FE}	200	_	450	_	I _C = -1A, V _{CE} = -2V	
		130		_		I _C = -2A, V _{CE} = -2V	
		80		_		I _C = -3A, V _{CE} = -2V	
			_	-90		I _C = -500mA, I _B = -50mA	
	V _{CE(sat)}	_		-180		$I_C = -1A$, $I_B = -50mA$	
Collector-Emitter Saturation Voltage (Note 10)				-320	mV	I _C = -2A, I _B = -100mA	
				-270		I _C = -2A, I _B = -200mA	
				-390		$I_C = -3A$, $I_B = -300mA$	
Equivalent On-Resistance	R _{CE(sat)}	1	67	135	mΩ	$I_C = -2A$, $I_B = -200mA$	
Base-Emitter Saturation Voltage (Note 10)	V _{BE(sat)}	_	_	-1.1	V	$I_C = -2A$, $I_B = -100mA$	
Base-Emitter Saturation voltage (Note 10)				-1.2		$I_C = -3A$, $I_B = -300mA$	
Base-Emitter Turn-On Current (Note 10)	V _{BE(on)}	1	_	-1.1	V	$I_{C} = -1A, V_{CE} = -2V$	
Transition Frequency	f⊤	100	_	_	MHz	I _C = -100mA, V _{CE} = -5V, f = 100MHz	
Collector Output Capacitance	C _{obo}	_	_	35	pF	V _{CB} = -10V, I _E = 0, f = 1MHz	
Turn-On Time	t _{on}	_	87	_	ns		
Delay Time	t _d	_	41	_	ns		
Rise Time	t _r	_	46	_	ns	V _{CC} = -30v,	
Turn-Off Time	t _{off}	_	294	_	ns	$I_{CC} = 150 \text{mA}$ $I_{B1} = -I_{B2} = 15 \text{mA}$	
Storage Time	ts	_	250	_	ns	IRZ = ISIIIV	
Fall Time	t _f		44	_	ns		

Note: 10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)



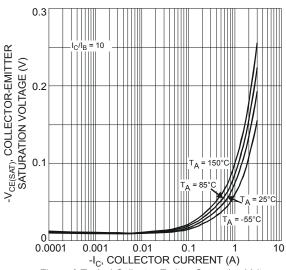


Figure 3 Typical Collector-Emitter Saturation Voltage vs. Collector Current

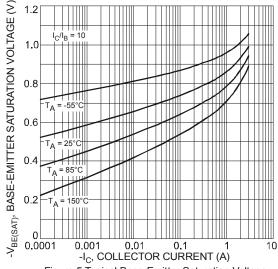
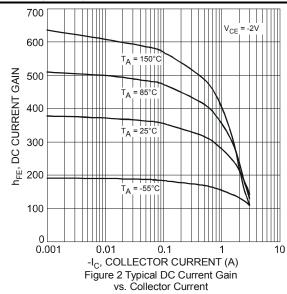


Figure 5 Typical Base-Emitter Saturation Voltage vs. Collector Current



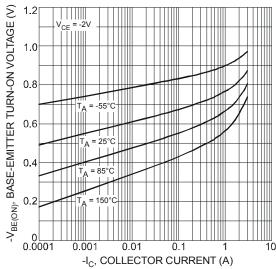


Figure 4 Typical Base-Emitter Turn-On Voltage vs. Collector Current

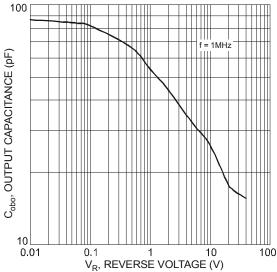


Figure 6 Typical Output Capacitance Characteristics



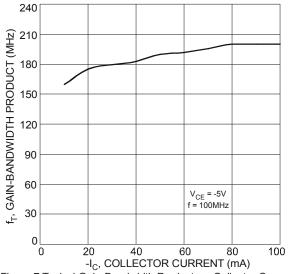
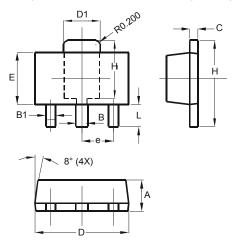


Figure 7 Typical Gain-Bandwidth Product vs. Collector Current

Package Outline Dimensions

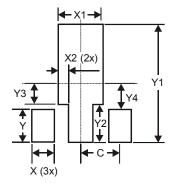
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT89				
Dim	Min	Max		
Α	1.40	1.60		
В	0.44	0.62		
B1	0.35	0.54		
C	0.35	0.44		
D	4.40	4.60		
D1	1.62	1.83		
Е	2.29	2.60		
е	1.50 Typ			
Н	3.94	4.25		
H1	2.63	2.93		
L	0.89	1.20		
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Х	0.900
X1	1.733
X2	0.416
Y	1.300
Y1	4.600
Y2	1.475
Y3	0.950
Y4	1.125
С	1.500

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